

isc N-Channel MOSFET Transistor

AOTF42S60L

• FEATURES

- Drain Current –I_D= 39A@ T_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage-: V_{DSS}= 600V(Min)
- Static Drain-Source On-Resistance
- : $R_{DS(on)}$ = 99m Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

• Be suitable for synchronous rectification for server and general purpose applications

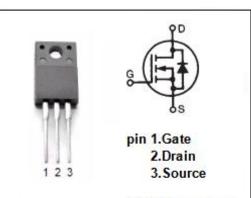
| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|-------------------------------------|---------------|------|
| V _{DSS} | Drain-Source Voltage | 600 | V |
| V _{GS} | Gate-Source Voltage | ±30 | V |
| ID | Drain Current-Continuous | 39 | А |
| I _{DM} | Drain Current-Single Pulsed 166 | | А |
| PD | Total Dissipation @Tc=25℃ | 37.9 | W |
| Tj | Max. Operating Junction Temperature | -55~150 | °C |
| T _{stg} | Storage Temperature | ature -55~150 | |

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

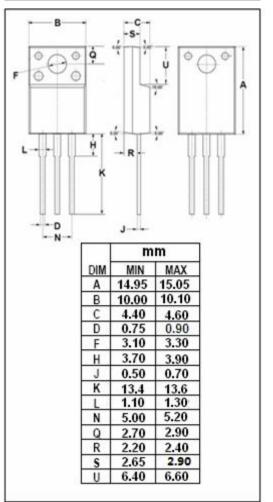
THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT |
|-----------|------------------------------------|-----|------|
| Rth(ch-c) | Channel-to-case thermal resistance | 3.3 | °C/W |

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TO-220F package



isc website: www.iscsemi.cn



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25\,^\circ\!\!\!\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYPE | МАХ | UNIT |
|---------------------|--------------------------------|---|-----|------|-----------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 250 μ A | 600 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = 5V; I _D = 250 μ A | 2.5 | | 3.8 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 21A V _{GS} = 10V; I _D = 21A;T _J = 150℃ | | | 99 280 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V_{GS} = ±30V; V_{DS} = 0V | | | ±100 | nA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 600V; V _{GS} = 0V V _{DS} = 480V; V _{GS} = 0V;T _J = 150°C | | 10 | 1 | μA |
| V _{SD} | Diode forward voltage | ls= 21A; V _{GS} = 0V | | 0.84 | | V |

NOTICE:

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